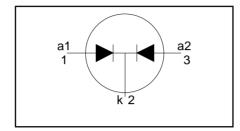
## PBYR1545CTF, PBYR1545CTX series

### **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Isolated mounting tab

### **SYMBOL**



### QUICK REFERENCE DATA

$$V_R = 40 \text{ V} / 45 \text{ V}$$
 $I_{O(AV)} = 15 \text{ A}$ 
 $V_F \le 0.57 \text{V}$ 

#### **GENERAL DESCRIPTION**

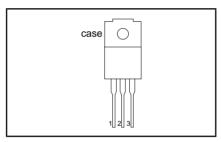
Dual, common cathode schottky rectifier diodes in a plastic envelope with electrically isolated mounting tab. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR1545CTF series is supplied in the SOT186 package. The PBYR1545CTX series is supplied in the SOT186A package.

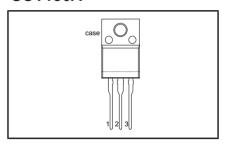
#### **PINNING**

PIN	DESCRIPTION		
1	anode 1 (a)		
2	cathode (k)		
3	anode 2 (a)		
tab	isolated		

#### **SOT186**



### SOT186A



### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER CONDITIONS		MIN.	МА	X.	UNIT
		PBYR15 PBYR15		40CTF 40CTX	45CTF 45CTX	
$V_{RRM}$	Peak repetitive reverse voltage		-	40	45	V
$V_{RWM}$	Working peak reverse voltage		-	40	45	V
$V_R$	Continuous reverse voltage	T <sub>hs</sub> ≤ 89 °C	-	40	45	V
I <sub>O(AV)</sub>	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{hs} \le 93$ °C	-	15	5	А
I <sub>FRM</sub>	Repetitive peak forward current per diode	square wave; $\delta = 0.5$ ; $T_{hs} \le 93 ^{\circ}C$	-	15	5	Α
I <sub>FSM</sub>	Non-repetitive peak forward current per diode	t = 10  ms t = 8.3  ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{RRM(max)}$	-	10 11		A A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-	1		A
$T_{j}$	Operating junction temperature	Jinax	-	15	0	°C
T <sub>stg</sub>	Storage temperature		- 65	17	5	°C

# PBYR1545CTF, PBYR1545CTX series

## **ISOLATION LIMITING VALUE & CHARACTERISTIC**

 $T_{hs} = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>isol</sub>	Peak isolation voltage from all terminals to external heatsink	SOT186 package; R.H. ≤ 65%; clean and dustfree	-	-	1500	V
V <sub>isol</sub>	R.M.S. isolation voltage from all terminals to external heatsink	SOT186A package; f = 50-60 Hz; sinusoidal waveform; R.H. ≤ 65%; clean and dustfree	-	-	2500	V
C <sub>isol</sub>	Capacitance from pin 2 to external heatsink	f = 1 MHz	-	10	-	pF

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-hs</sub>	Thermal resistance junction	per diode	-	-	6	K/W
	to heatsink	both diodes (with heatsink compound)	-	-	5.2	K/W
$R_{thj-a}$	Thermal resistance junction to ambient	in free air	-	55	-	K/W

## **ELECTRICAL CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V <sub>F</sub>	Forward voltage	$I_F = 7.5 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.44	0.57	V
·		$I_{\rm F} = 15  \text{A};  T_{\rm i}' = 125  ^{\circ} \text{C}$	-	0.63	0.72	V
		$I_{\rm F} = 15  \text{A}^{\circ}$	-	0.62	0.84	V
I <sub>R</sub>	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	0.22	1	mΑ
1		$V_R = V_{RWM_i}$ ; $T_j = 100^{\circ}$ C $V_R = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ , $T_i = 25^{\circ}$ C to 125°C	-	18	25	mΑ
$C_d$	Junction capacitance	$V_R = 5 \text{ V}$ ; f = '1 MHz, $T_j = 25 ^{\circ}\text{C}$ to 125 $^{\circ}\text{C}$	-	270	-	pF

## PBYR1545CTF, PBYR1545CTX series

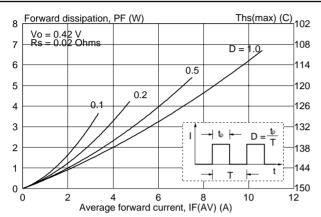


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

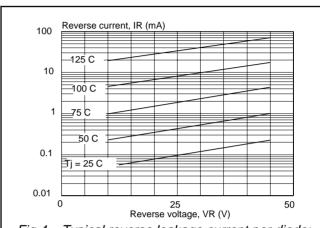


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

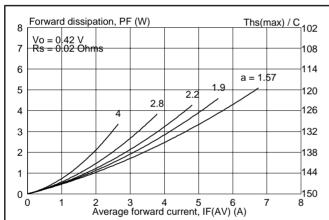


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

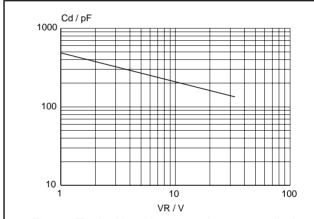


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125°C.

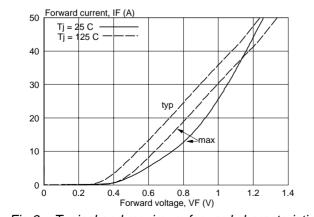


Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 

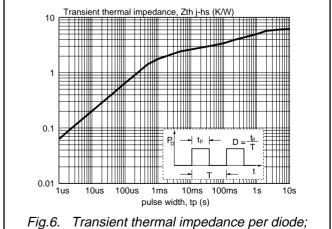
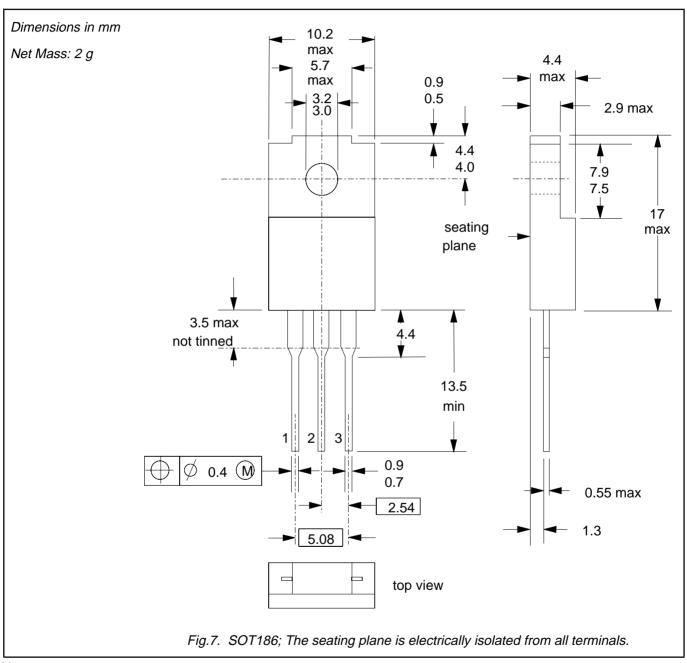


Fig.6. Transient thermal impedance per diode;  $Z_{th j ext{-}hs} = f(t_p)$ .

# PBYR1545CTF, PBYR1545CTX series

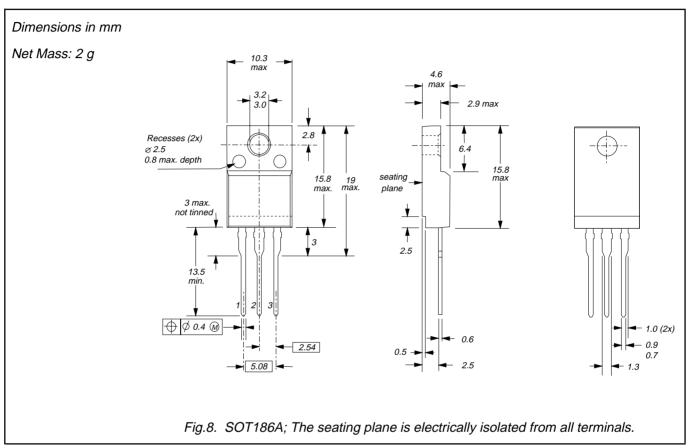
### **MECHANICAL DATA**



- Refer to mounting instructions for F-pack envelopes.
   Epoxy meets UL94 V0 at 1/8".

# PBYR1545CTF, PBYR1545CTX series

## **MECHANICAL DATA**



- Notes
  1. Refer to mounting instructions for F-pack envelopes.
  2. Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

## Rectifier diodes Schottky barrier

## PBYR1545CTF, PBYR1545CTX series

#### **DEFINITIONS**

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published lat				
Product specification This data sheet contains final product specifications.				

# Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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